

Patent Certificate No.: 4907613

Patent Certificate for Invention

Title of invention: LAYERED GaAs, METHOD OF PREPARING SAME, AND GaAs NANOSHEET EXFOLIATED FROM SAME

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Patent No.: ZL 201910420208.1

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Patentee: INDUSTRY-ACADEMIC COOPERATION FOUNDATION, YONSEI UNIVERSITY

Address: Seoul (KR)

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In accordance with the Patent Law, it is found after examination that there is no ground for rejection of the above-identified application, the Patent Office made a decision to grant patent right, issue this patent certificate and register it in the patent register. The patent right took effect from the date of announcement of grant of patent right. The duration of patent right for this patent shall be twenty years, counted from the filing date of the application.

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Applicant and Inventors filed on the filing date:

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证书号第 4907613 号



发明专利证书

发明名称：层状 GaAs、其制备方法及由此剥离的 GaAs 纳米片

发明人：沈祐永；崔相珍；金慧修

专利号：ZL 2019 1 0420208.1

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证书号第 4907613 号



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